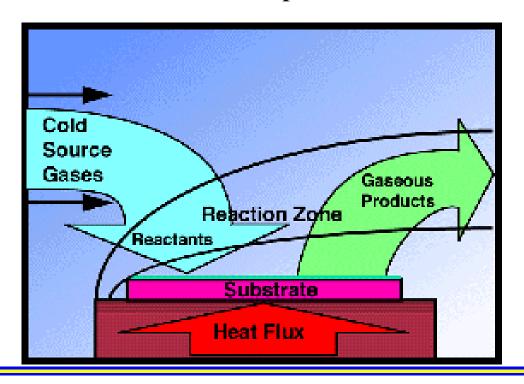
## **Chemical Vapor Deposition**

- A process wherein chemically reactive gases are used to deposit a thin film on a solid substrate
- > CVD requires some sort of energy input to dissociate the precursors to form reactive intermediates that deposit on the substrate.





### **Jargon of CVD:**

### Classification by "source of energy input"

#### (1) Thermal Chemical Vapor Deposition (CVD)

heat the gas and/or the substrate

$$SiH_{4-x}Cl_{x(g)} + H_{2(g)} \xrightarrow{heat(1050-1450 K)} Si_{(s)} + x HCl + (3-x)H_2$$
  $x = 0, 2, 3, 4$ 

- (2) Plasma Enhanced Chemical Vapor Deposition (PECVD)
  - excitation by electrons in a plasma where the electrons are accelerated by an electric field

$$SiH_4 + e^-_{fast} \xrightarrow{plasma} SiH_x + (4-x)H + e^-_{slow} \rightarrow Si_{(s)} + 2H_2 + e^-_{slow} \quad x = 0-3$$

$$3SiH_4 + 4NH_3 \xrightarrow{plasma} Si_3N_{4(s)} + 12H_2$$

#### (3) Photolytic CVD

excitation by light source, laser or broadband

$$SiH_4 + 2N_2O \xrightarrow{hv (Hg \ lamp)} SiO_{2(s)} + 2N_2 + 2H_2$$

$$In(CH_3)_3 + P(CH_3) + 2H_2 \xrightarrow{hv} InP_{(s)} + 4CH_4$$



#### **CVD** Classification by pressure regime

- (1) Atmospheric pressure CVD (APCVD) (760 Torr)
- (2) Subatmospheric CVD (10s of Torr to 760 Torr)
- (3) Low pressure CVD (LPCVD) (0.01-10 Torr)
- (4) Ultra High Vacuum CVD (UHV-CVD)
  - The lowest pressure the chamber can reach is ~10⁻⁰ Torr but depositions are done 10⁻⁶-10⁻³ Torr



# CVD Classification by gas precursor / film structure / growth mechanism

#### (1) Metalorganic CVD (MOCVD)

 Gas precursors are low boiling point organometallic liquids or solids that can be sublimed w/o decomposition

#### (2) Epitaxy or Vapor Phase Epitaxy

- For growing low defect density single crystal layers
- Homoepitaxy: (film and substrate are the same material)
- Heteroepitaxy: (film and substrate are different materials)

#### (3) Nonepitaxial growth

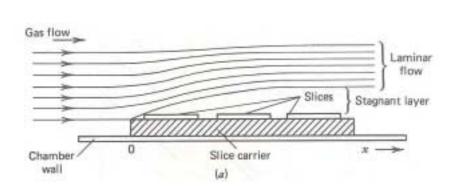
Polycrystalline or amorphous films

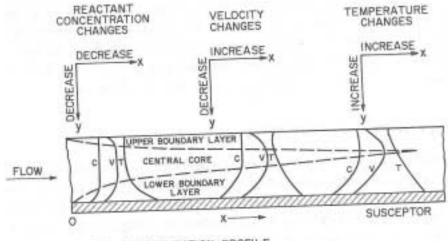
#### (4) Atomic Layer Deposition (ALD) or Atomic Layer Epitaxy (ALE)

Growing the films one atomic layer at a time



## **Horizontal CVD Reactors**

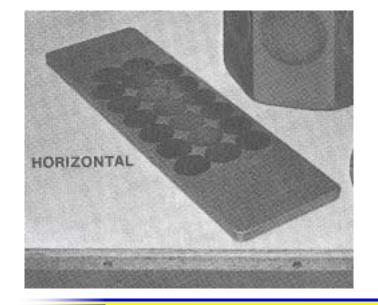


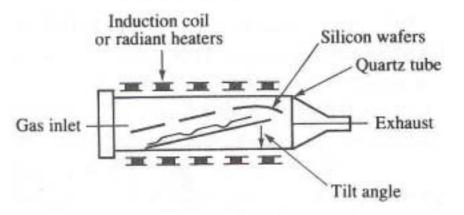


C - CONCENTRATION PROFILE

V - VELOCITY PROFILE

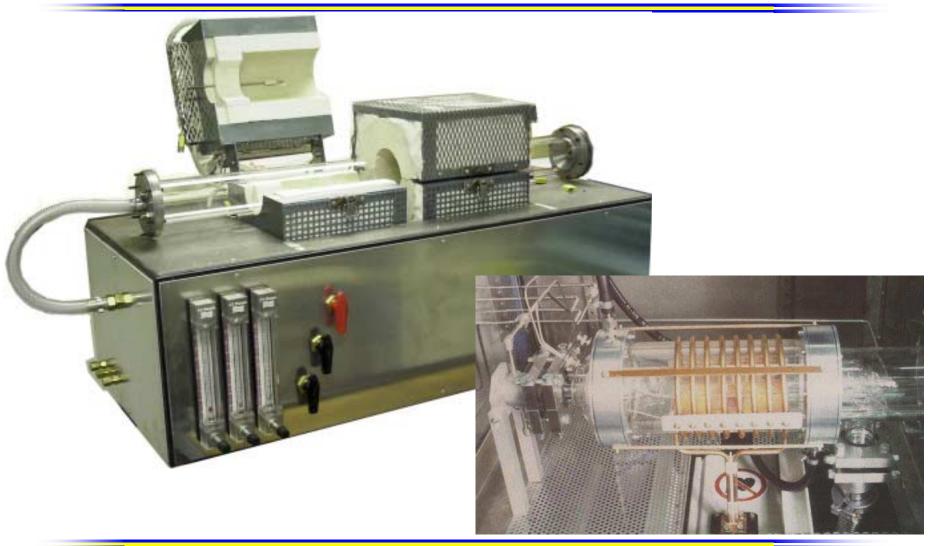
T - TEMPERATURE PROFILE





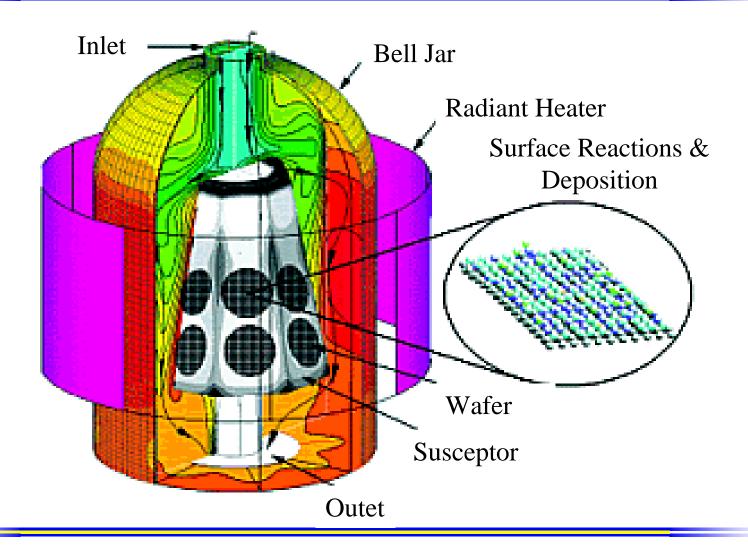


# **Horizontal CVD Reactors**



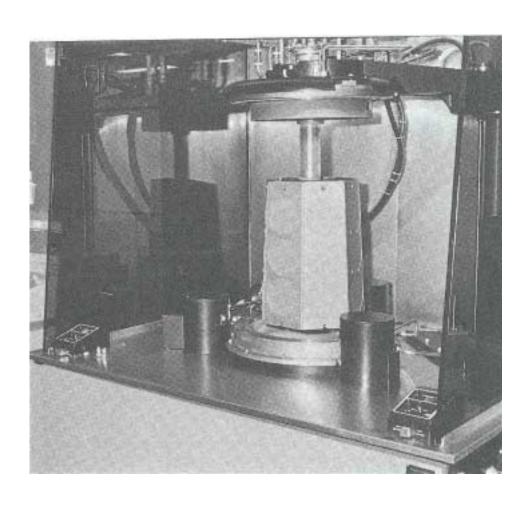


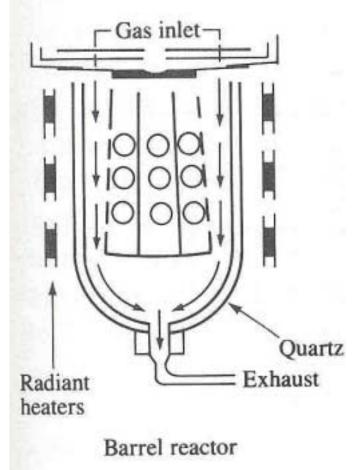
## The Barrel Reactor





## The Barrel Reactor

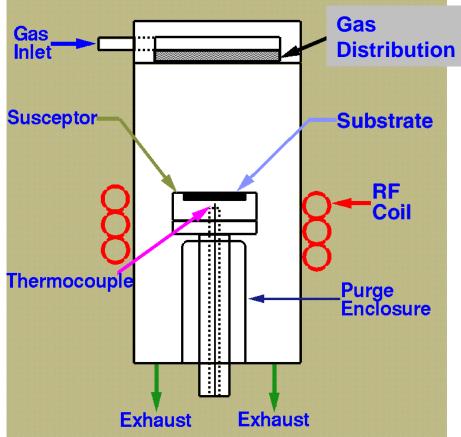






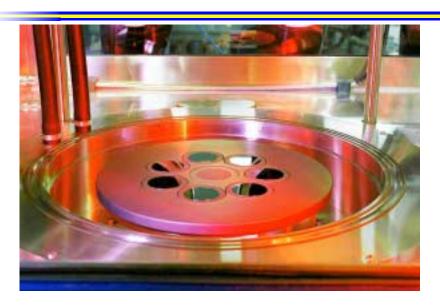
# (Rotating Disk) Vertical CVD Reactor



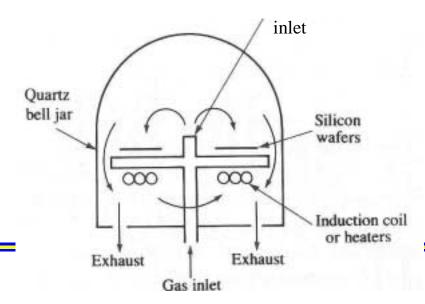




# Pancake or Planetary CVD Reactor

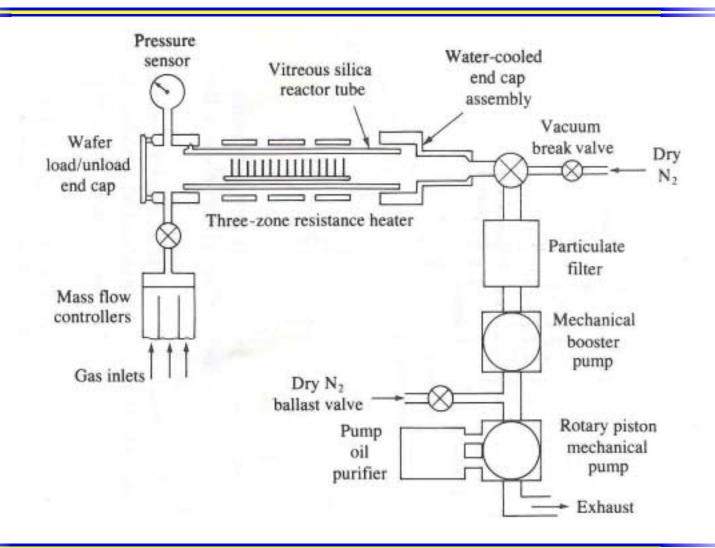






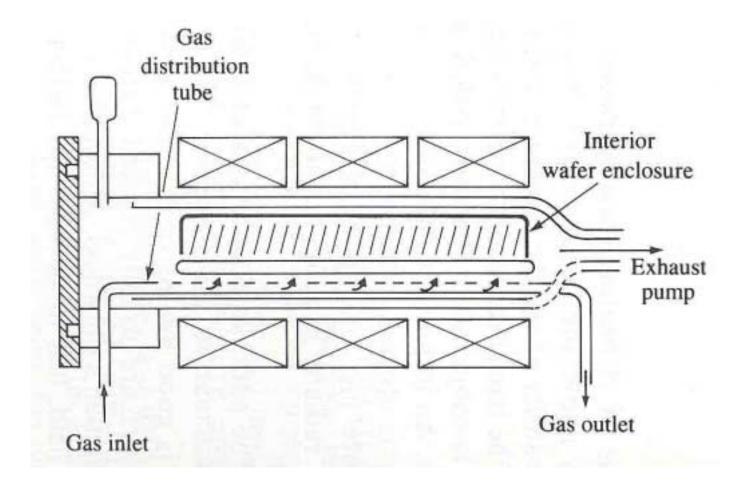


## **LPCVD** Reactor





## **Distributed Feed LPCVD Reactor**

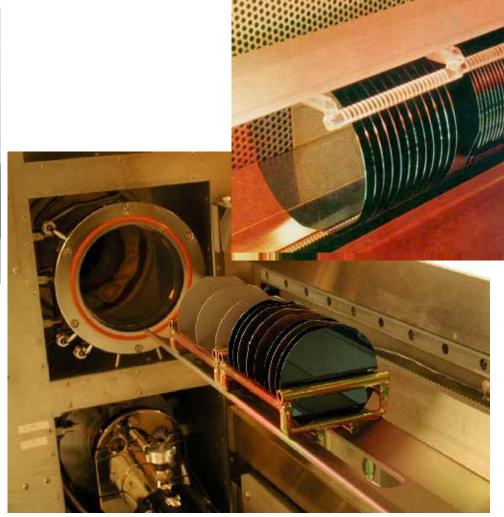




## **LPCVD** Reactor









# **LPCVD Systems**





